

# 4V Drive Nch MOSFET

## RP1E100XN

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (MPT6).

### ● Application

Switching

### ● Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	1000
RP1E100XN		○

### ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DSS}$	30	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	Continuous	$I_D$	$\pm 10$ A
	Pulsed	$I_{DP}$ *1	$\pm 36$ A
Source current (Body Diode)	Continuous	$I_S$	1.6 A
	Pulsed	$I_{SP}$ *1	36 A
Power dissipation	$P_D$ *2	2.0	W
Channel temperature	Tch	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

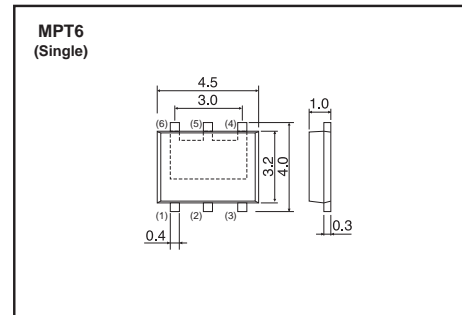
\*2 Mounted on a ceramic board.

### ● Thermal resistance

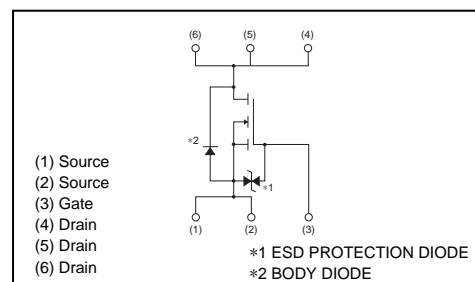
Parameter	Symbol	Limits	Unit
Channel to Ambient	$R_{th}(ch-a)$ *	62.5	°C / W

\*Mounted on a ceramic board.

### ● Dimensions (Unit : mm)



### ● Inner circuit



- (1) Source
- (2) Source
- (3) Gate
- (4) Drain
- (5) Drain
- (6) Drain

\*1 ESD PROTECTION DIODE  
\*2 BODY DIODE

● **Electrical characteristics** (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	9.5	13	mΩ	$I_D=10A, V_{GS}=10V$
		-	12	17		$I_D=10A, V_{GS}=4.5V$
		-	13	18		$I_D=10A, V_{GS}=4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	8.0	-	-	S	$I_D=10A, V_{DS}=10V$
Input capacitance	$C_{iss}$	-	800	-	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	-	270	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	140	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	10	-	ns	$I_D=5A, V_{DD} \approx 15V$
Rise time	$t_r^*$	-	45	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	50	-	ns	$R_L=3.0\Omega$
Fall time	$t_f^*$	-	15	-	ns	$R_G=10\Omega$
Total gate charge	$Q_g^*$	-	11.0	-	nC	$I_D=10A, V_{DD} \approx 15V$
Gate-source charge	$Q_{gs}^*$	-	2.4	-	nC	$V_{GS}=5V$
Gate-drain charge	$Q_{gd}^*$	-	4.8	-	nC	

\*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.2	V	$I_S=10A, V_{GS}=0V$

\*Pulsed

● Electrical characteristic curves

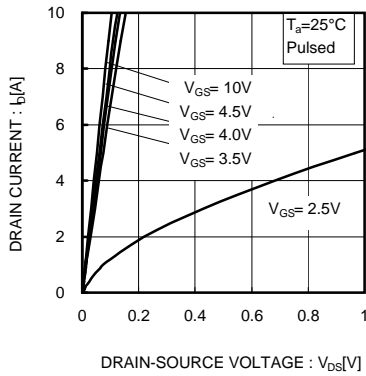


Fig.1 Typical Output Characteristics ( I )

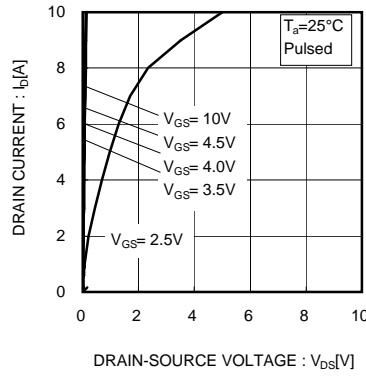


Fig.2 Typical Output Characteristics ( II )

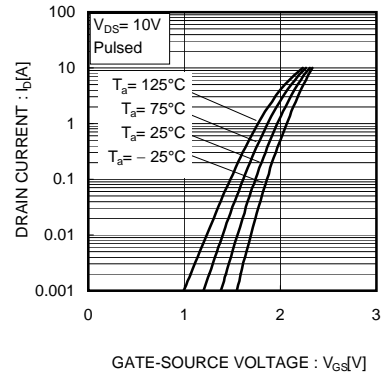


Fig.3 Typical Transfer Characteristics

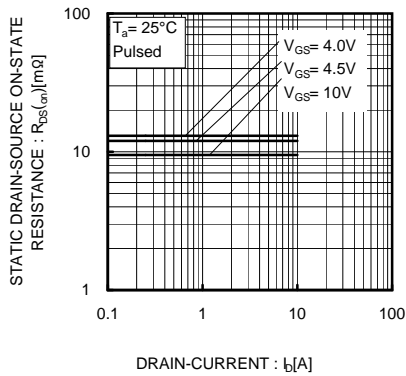


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current ( I )

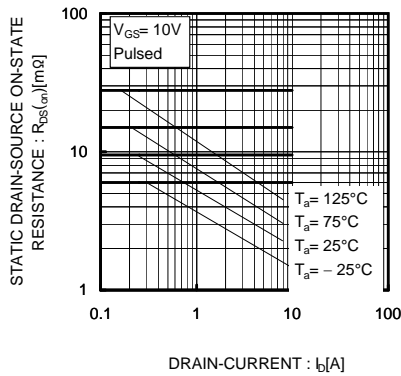


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current ( II )

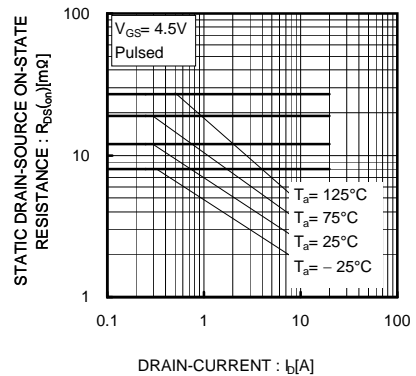


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current ( III )

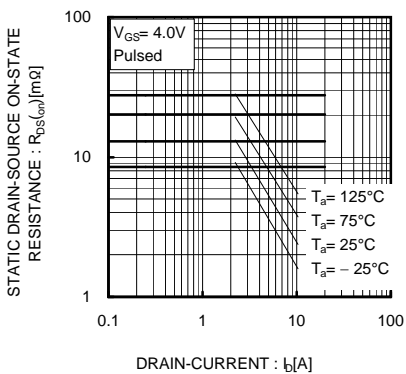


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current ( IV )

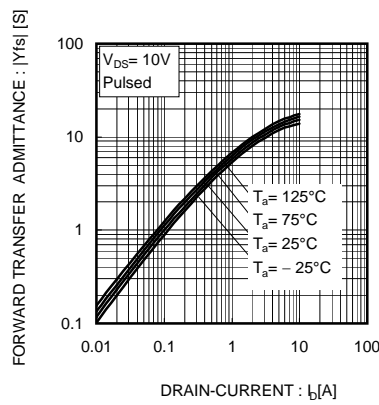


Fig.8 Forward Transfer Admittance vs. Drain Current

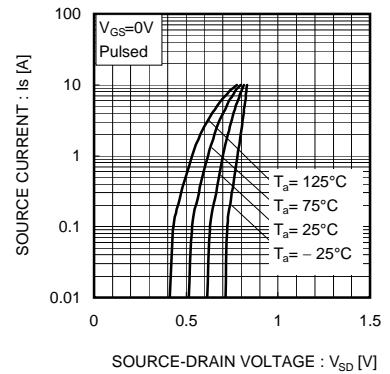


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

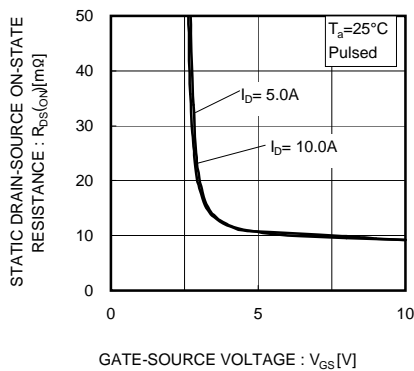


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

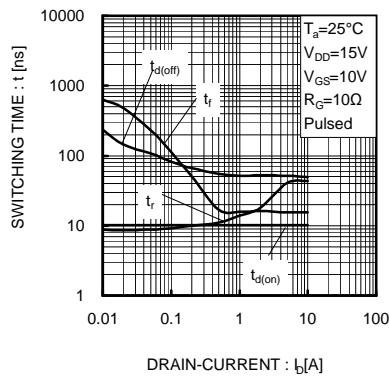


Fig.11 Switching Characteristics

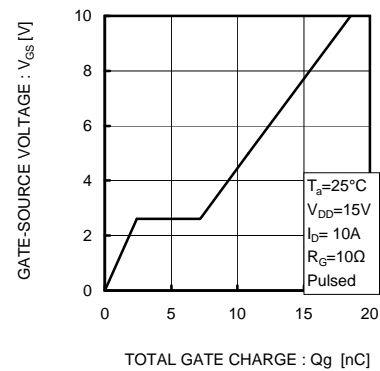


Fig.12 Dynamic Input Characteristics

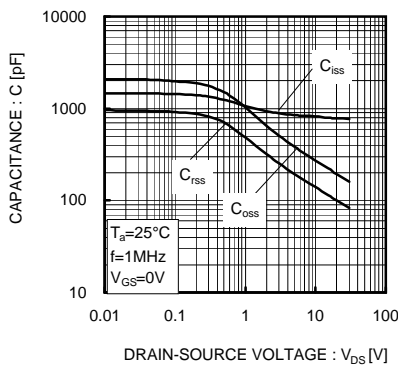


Fig.13 Typical Capacitance vs. Drain-Source Voltage

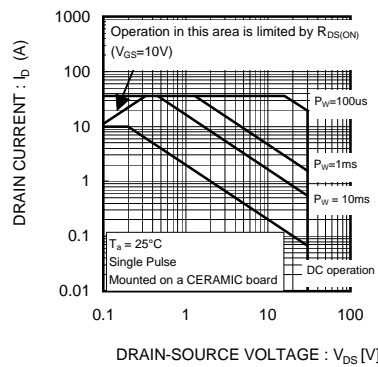


Fig.14 Maximum Safe Operating Area

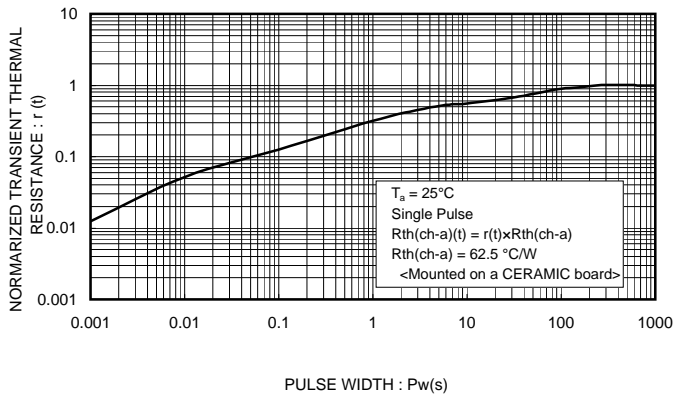


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

● Measurement circuits

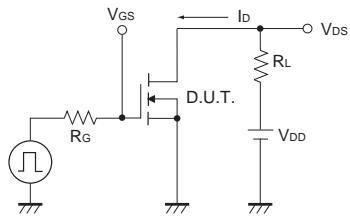


Fig.1-1 Switching time measurement circuit

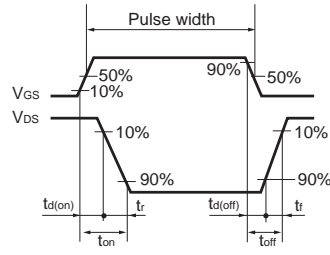


Fig.1-2 Switching waveforms

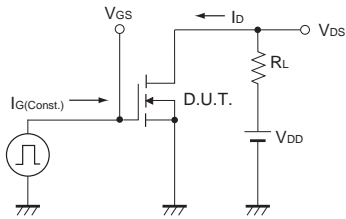


Fig.2-1 Gate charge measurement circuit

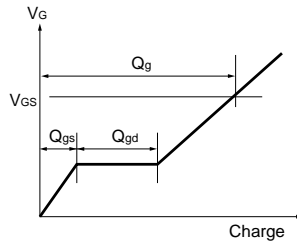


Fig.2-2 Gate Charge Waveform

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